

IN THE SPECIFICATION

Please insert the following sub-heading at page 1, between prenumbered lines 9 and 10 as follows:

FIELD OF THE INVENTION

Please insert the following sub-heading at page 1, between prenumbered lines 14 and 15 as follows:

DISCUSSION OF THE BACKGROUND

Please replace the paragraphs at page 3, lines 8-16, with the following rewritten paragraph:

This clamp circuit operates at the voltage more than Vdd. To meet this need, the n zener diodes 1 are connected in series. And if the potential difference between the Vdd terminal and the Vo terminal becomes above ($n \times V_z$), the clamp circuit begins to operate. In the case of this circuit, the Vdd terminal corresponds to the terminal PK in FIG. 16, and the base of the NPN-transistor 20 corresponds to the terminal PA in FIG. 16.

Please replace the paragraph at page 3, lines 16-21, with the following rewritten paragraph:

A serge surge absorption circuit with zener diodes provided in a regeneration control system for inductive load is disclosed in Japanese Patent Laid-Open Disclosure No. 10-136564. The diode for preventing an adverse current is connected in series to the zener diode as a serge surge absorption element in this serge surge absorption circuit.